

JMV3708NA

Product Preview

25V 50A N-Channel MOSFET

Features

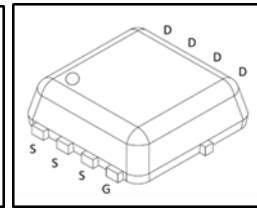
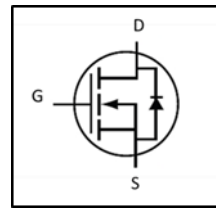
- Advanced shielded-gate technology
- Ultra-low on-resistance and gate-charge
- RoHS compliant
- 100% avalanche tested



Product Summary	
V_{DS}	25V
$R_{DS(ON)}$	1.7 m Ω (Typ.)
	2.2 m Ω (Max.)
I_D	50A

Applications

- Motor controllers
- DC-to-DC convertors
- Battery-driven electronic products, electrical equipment and machines


Ordering Information

Part Number	Marking	Package	Packaging
JMV3708NA	3708NA	DFN3.3x3.3	Tape & Reel

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Drain-to-Source Voltage	V_{DS}	25	V
Gate-to-Source Voltage	V_{GS}	± 10	
Continuous Drain Current, Package limited ($T_C = 25^\circ\text{C}$) ⁽¹⁾	I_D	50	A
Continuous Drain Current, Silicon limited ($T_C = 25^\circ\text{C}$) ⁽¹⁾	I_D	130	
Continuous Drain Current, Silicon limited ($T_C = 100^\circ\text{C}$) ⁽¹⁾	I_D	80	
Continuous Drain Current, Silicon limited ($T_A = 25^\circ\text{C}$) ^{(2), (5)}	I_D	25	
Continuous Drain Current, Silicon limited ($T_A = 100^\circ\text{C}$) ^{(2), (5)}	I_D	17	
Pulsed Drain Current ⁽³⁾	I_{DM}	200	
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	56.8	W
Linear Derating Factor	-	0.45	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	76	mJ
Avalanche Current	I_{AS}	26	A
Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	

Thermal Characteristics

Parameter	Symbol	Max	Unit
Junction-to-Ambient Thermal Resistance ⁽⁵⁾	$R_{\theta JA}$	55	$^\circ\text{C}/\text{W}$
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	2.2	

Static Electrical Characteristics⁽⁶⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	25	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.4	-	1.2	
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 10\text{V}$	-	-	± 100	nA
Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$	-	1.7	2.2	m Ω
		$V_{GS} = 2.5\text{V}, I_D = 10\text{A}$	-	2.5	3.2	m Ω

Dynamic Electrical Characteristics ⁽⁶⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Transconductance	g_{fs}	$V_{DS} = 5V, I_D = 15A$	-	110	-	S
Total Gate Charge	Q_g	$V_{GS} = 4.5V,$ $V_{DS} = 15V,$ $I_D = 20A$	-	28.1	-	nC
Gate-to-Source Charge	Q_{gs}		-	5.6	-	
Gate-to-Drain Charge	Q_{gd}		-	6.6	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V$ $I_D = 15A,$ $R_G = 3.0$	-	13	-	ns
Rise Time	t_r		-	4	-	
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	
Fall Time	t_f		-	8	-	
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$	-	3611	-	pF
Output Capacitance	C_{oss}		-	1856	-	
Reverse Transfer Capacitance	C_{rss}		-	73	-	

Diode Characteristics ⁽⁶⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 10A$	-	0.7	-	V
Reverse Recovery Time	T_{rr}	$V_{GS} = 0V, I_S = 20A,$ $dI_S/dt = 100A/\mu s$	-	26	-	ns
Reverse Recovery Charge	Q_{rr}		-	33	-	nC

(1) Rated according to $R_{\theta JC}$.

(2) Rated according to $R_{\theta JA}$.

(3) Limited by maximum T_J .

(4) $T_A = 25^\circ C, L = 0.1mH, I_{AS} = 26A$.

(5) Surface-mounted on 1 inch² FR4 board, 2 oz Cu.

(6) $T_J = 25^\circ C$ unless otherwise specified.

Typical Electrical Characteristics

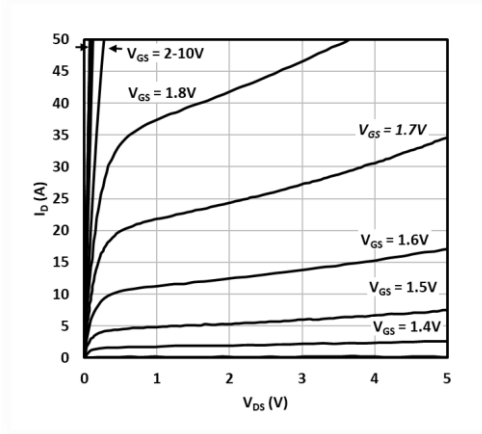


Fig. 1 Output characteristics

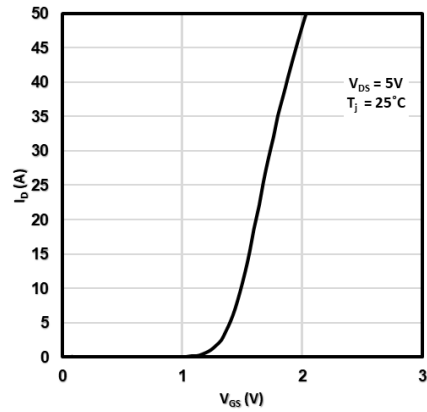


Fig. 2 Transfer characteristics

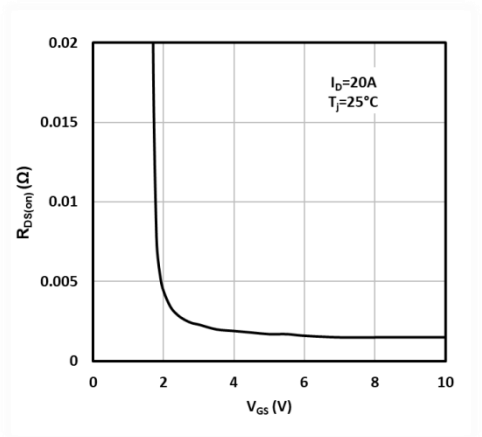


Fig.3 On-resistance vs. gate voltage

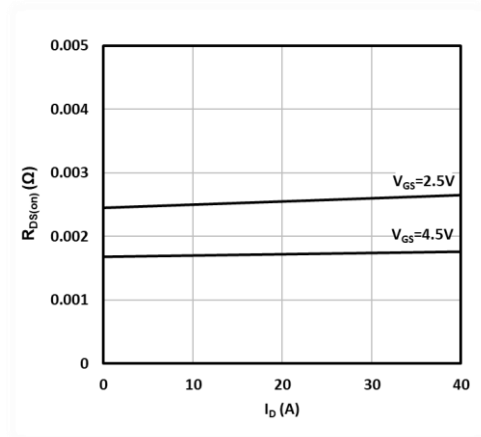


Fig.4 On-resistance vs. drain current

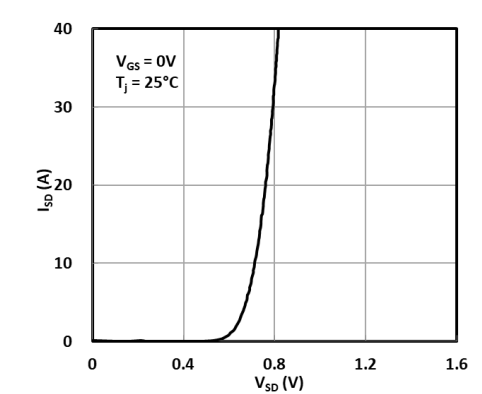


Fig.5 Source-to-drain diode forward characteristics

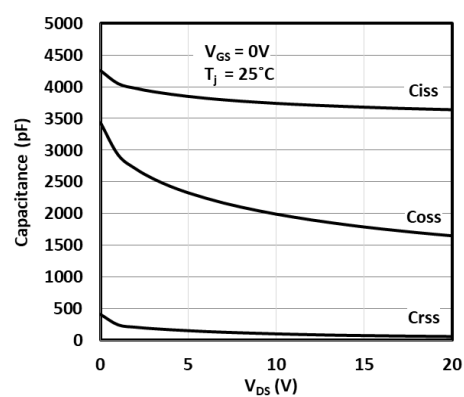


Fig.6 Capacitance vs. drain-to-source voltage

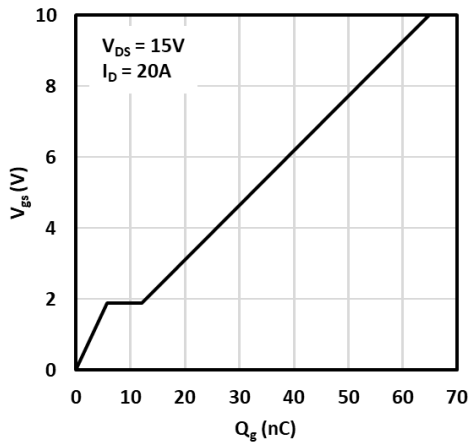


Fig.7 Gate-to-source voltage vs. gate charge

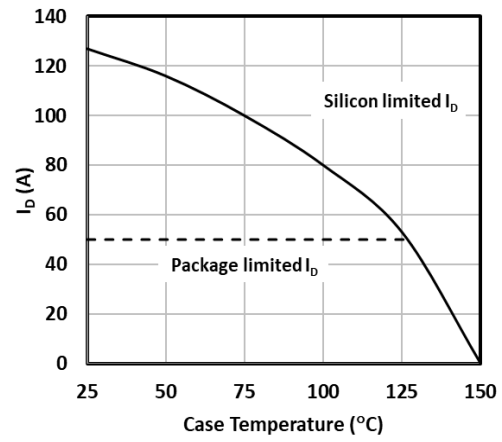


Fig.8 Maximum drain current vs. case temperature

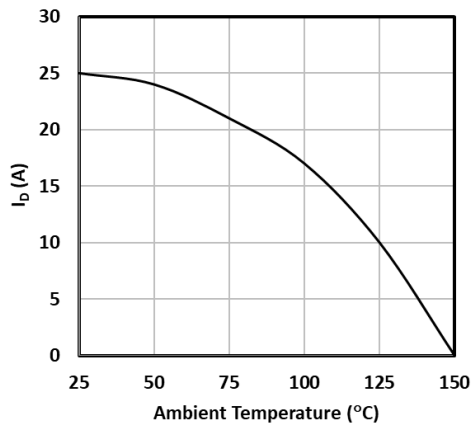
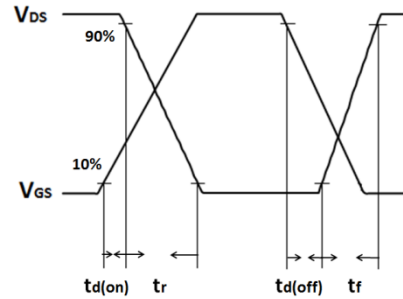
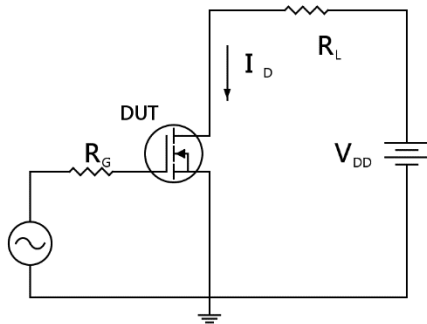
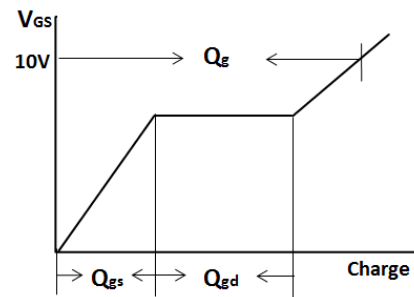
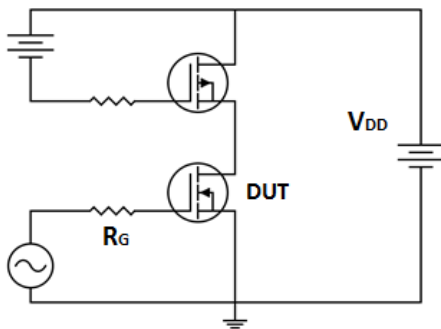


Fig. 9 Maximum drain current vs. ambient temperature

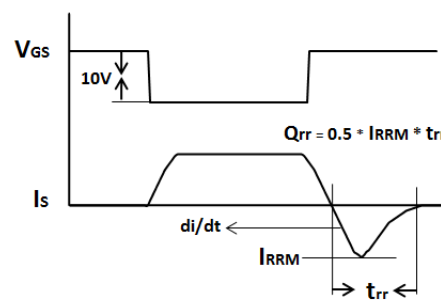
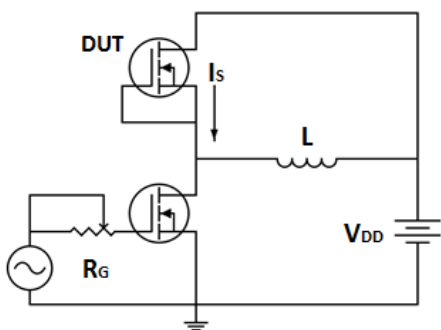
Test Circuits and Waveforms



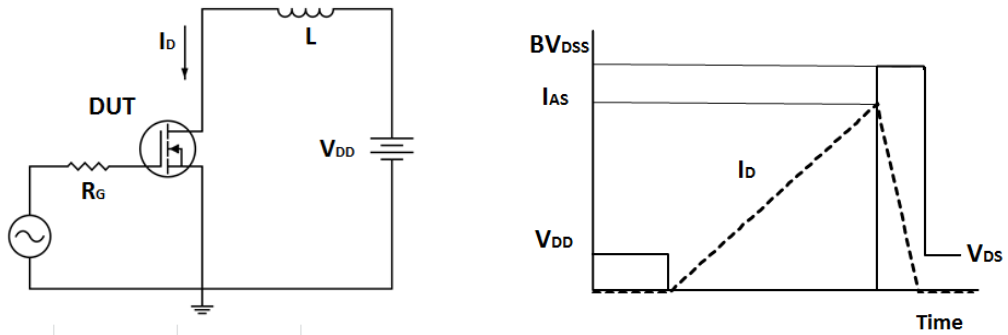
Resistive switching time test circuit & waveforms



Gate charge test circuit & waveform

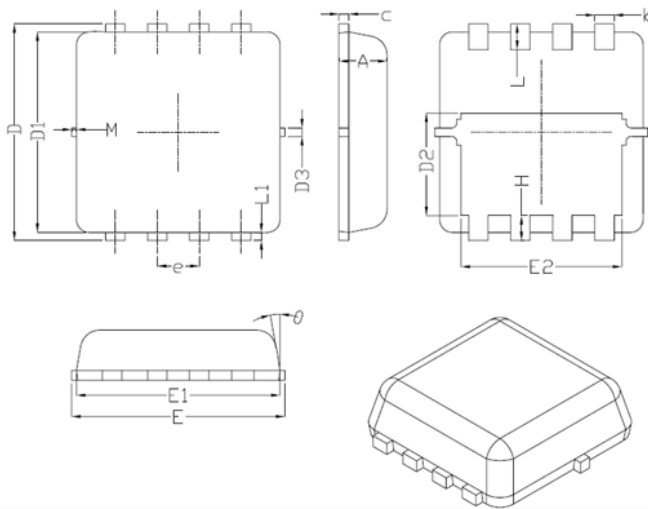


Peak diode recovery dv/dt test circuit & waveforms



Unclamped inductive switching test circuit & waveforms

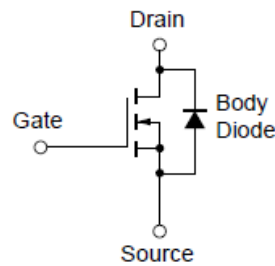
Package Drawing



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
b	0.25	0.32	0.39
c	0.10	0.15	0.25
D	3.00	3.30	3.60
D1	3.00	3.10	3.50
D2	1.48	2.00	2.20
D3	--	0.20	--
E	3.00	3.30	3.60
E1	3.00	3.10	3.25
E2	2.29	2.49	2.69
e	0.65 BSC		
H	0.15	0.25	0.50
L	0.15	0.40	0.60
L1	0.05	0.15	0.25
α	8°	10°	12°
M	--	0.10	--

DFN 3.3x3.3

Equivalent Circuit



Revision history of JMV3708NA Specification

Version	Change Items	Effective Date
1.00	Initial Release	09-Mar-20

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